74HC1G86; 74HCT1G86

2-input EXCLUSIVE-OR gate Rev. 04 — 20 July 2007

Product data sheet

General description 1.

74HC1G86 and 74HCT1G86 are high-speed Si-gate CMOS devices. They provide a 2-input EXCLUSIVE-OR function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC/HCT86.

2. **Features**

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- Specified from -40 °C to +125 °C

Ordering information 3.

Ordering information Table 1.

Type number	Package							
	Temperature range	Name	Description	Version				
74HC1G86GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package;	SOT353-1				
74HCT1G86GW			5 leads; body width 1.25 mm					
74HC1G86GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753				
74HCT1G86GV								

Marking

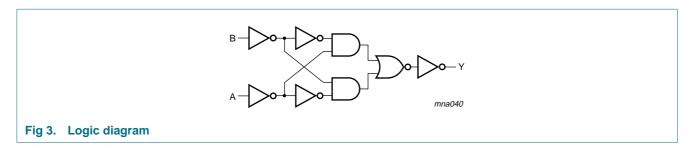
Table 2. Marking codes

3	
Type number	Marking
74HC1G86GW	НН
74HCT1G86GW	TH
74HC1G86GV	H86
74HCT1G86GV	T86



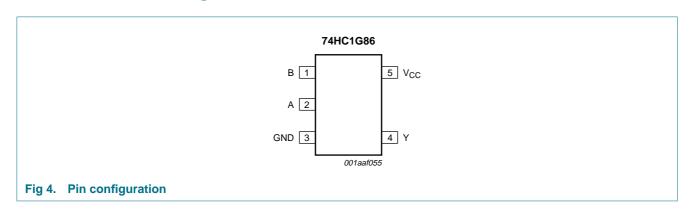
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
В	1	data input
Α	2	data input
GND	3	ground (0 V)
Υ	4	data output
V_{CC}	5	supply voltage

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7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Inputs	Output	
Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I _{CC}	supply current		-	25	mA
I_{GND}	ground current		-25	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	200	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions	74HC1G86			74HCT1G86			Unit
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 \text{ V}$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

^[2] Above 55 $^{\circ}\text{C}$ the value of P $_{tot}$ derates linearly with 2.5 mW/K.

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	-40	–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	
For type	74HC1G86					•		
V_{IH}	HIGH-level input	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
	voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V_{IL}	LOW-level input	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
	voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	V
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V_{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 20 \mu A$; $V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A$; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A$; $V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
		$I_{O} = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	1.0	-	1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μΑ
Cı	input capacitance		-	1.5	-	-	-	pF
For type	74HCT1G86							
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	8.0	V
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_{O} = -20 \mu A$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	V
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 20 \mu A$; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μΑ

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 Table 7.
 Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C t	Unit	
			Min	Тур	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	10	-	20	μΑ
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $V_I = V_{CC} - 2.1 \text{ V};$ $I_O = 0 \text{ A}$	-	-	500	-	850	μΑ
C _I	input capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f \le 6.0$ ns; All typical values are measured at $T_{amb} = 25$ °C. For test circuit see Figure 6

Symbol	Parameter	Conditions		-40 °C to +8		5 °C	-40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	
For type	74HC1G86	'						'	
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		-	22	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	11	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	9	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		-	9	20	-	23	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}$	[2]	-	23	-	-	-	pF
For type	74HCT1G86								
t _{pd}	propagation delay	A and B to Y; see Figure 5	[1]						
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	13	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	10	-	-	-	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	[2]	-	23	-	-	-	pF

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz

f_o = output frequency in MHz

C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

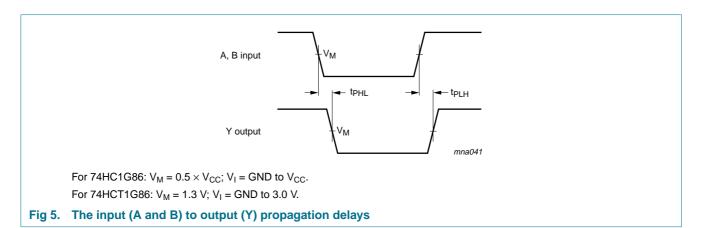
 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$

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^[2] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

6 of 11

12. Waveforms



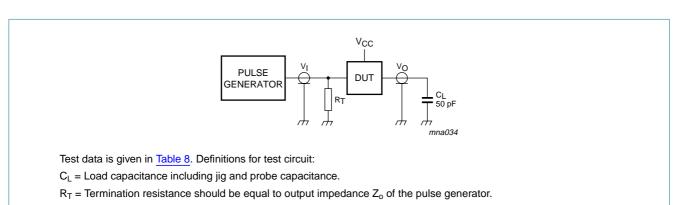


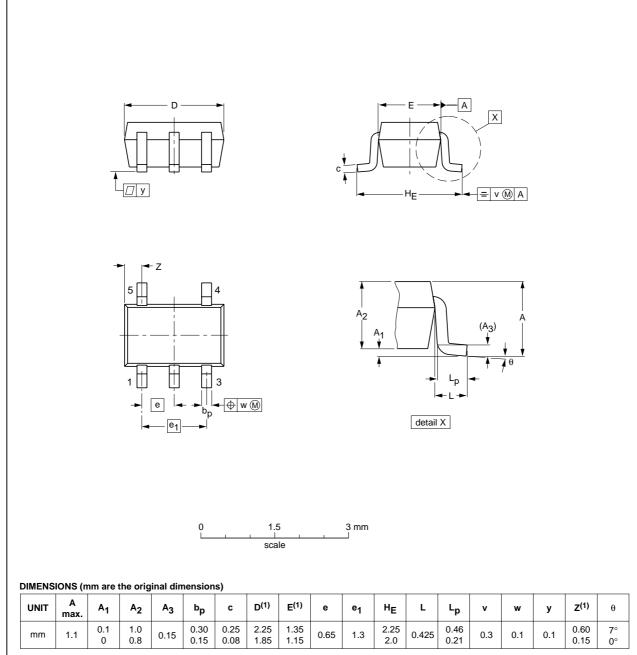
Fig 6. Load circuitry for switching times

Product data sheet

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	REFERENCES		EUROPEAN		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT353-1		MO-203	SC-88A			00-09-01 03-02-19	

Fig 7. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

8 of 11

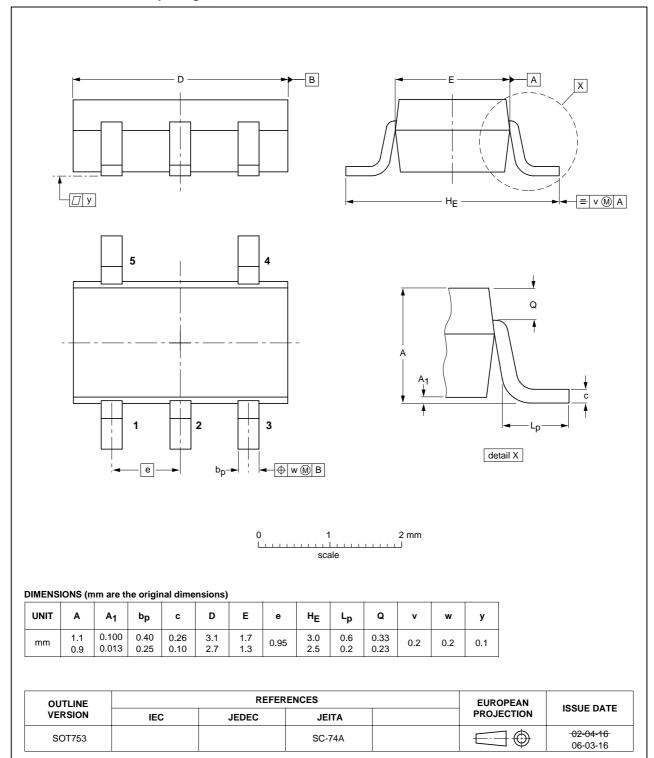


Fig 8. Package outline SOT753 (SC-74A)

Product data sheet

14. Abbreviations

Table 9. Abbreviations

Acronym	Description
DUT	Device Under Test
TTL	Transistor-Transistor Logic

15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
74HC_HCT1G86_4	20070720	Product data sheet	-	74HC_HCT1G86_3				
Modifications:	eations: • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.							
	 Legal texts 	s have been adapted to the r	new company name whe	ere appropriate.				
	 Package S 	SOT353 changed to SOT353	-1 in <u>Table 1</u> and <u>Figure</u>	<u>· 7</u> .				
	 Quick Refe 	erence Data and Soldering s	ections removed.					
	 Section 2 	"Features" updated.						
74HC_HCT1G86_3	20020515	Product specification	-	74HC_HCT1G86_2				
74HC_HCT1G86_2	20010406	Product specification	-	74HC_HCT1G86_1				
74HC_HCT1G86_1	19980805	Product specification	-	-				

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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18. Contents

1	General description	1
2	Features	1
3	Ordering information	1
4	Marking	1
5	Functional diagram	2
6	Pinning information	2
6.1	Pinning	2
6.2	Pin description	2
7	Functional description	3
8	Limiting values	3
9	Recommended operating conditions	3
10	Static characteristics	4
11	Dynamic characteristics	5
12	Waveforms	6
13	Package outline	7
14	Abbreviations	9
15	Revision history	9
16	Legal information 1	0
16.1	Data sheet status	C
16.2	Definitions1	C
16.3	Disclaimers	
16.4	Trademarks1	
17	Contact information 1	0
12	Contents 1	1

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